

**N-Channel Enhancement Mode Power MOSFET**

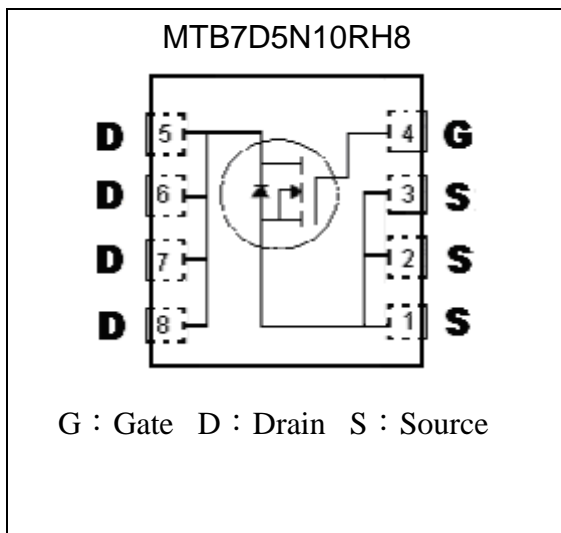
# MTB7D5N10RH8

**Features**

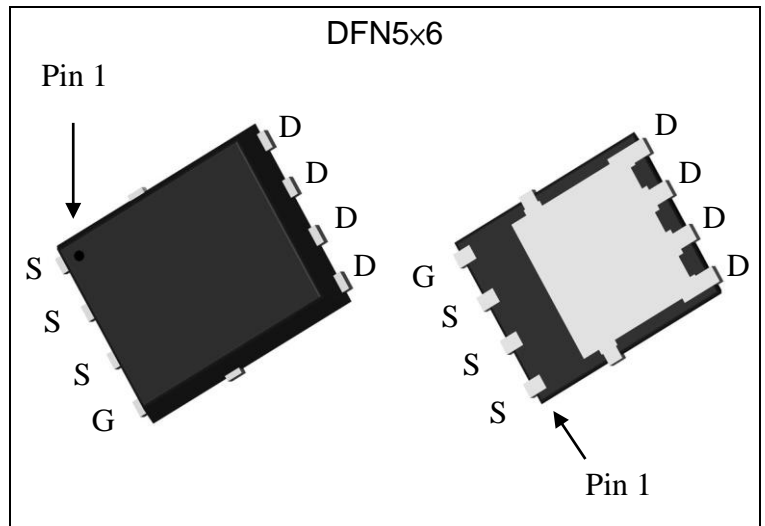
- Low On Resistance
- Simple Drive Requirement
- Low Gate Charge
- Fast Switching Characteristic
- RoHS compliant package

|  |                     |
|--|---------------------|
| <b>BV<sub>DSS</sub></b>  | <b>110V</b>         |
| <b>I<sub>D</sub>@V<sub>GS</sub>=10V, T<sub>C</sub>=25°C</b>      | <b>53A</b>          |
| <b>I<sub>D</sub>@V<sub>GS</sub>=10V, T<sub>A</sub>=25°C</b>      | <b>11.8A</b>        |
| <b>R<sub>DS(ON)</sub>@V<sub>GS</sub>=10V, I<sub>D</sub>=20A</b>  | <b>6.4mΩ (typ)</b>  |
| <b>R<sub>DS(ON)</sub>@V<sub>GS</sub>=4.5V, I<sub>D</sub>=16A</b> | <b>9.3 mΩ (typ)</b> |

**Symbol**

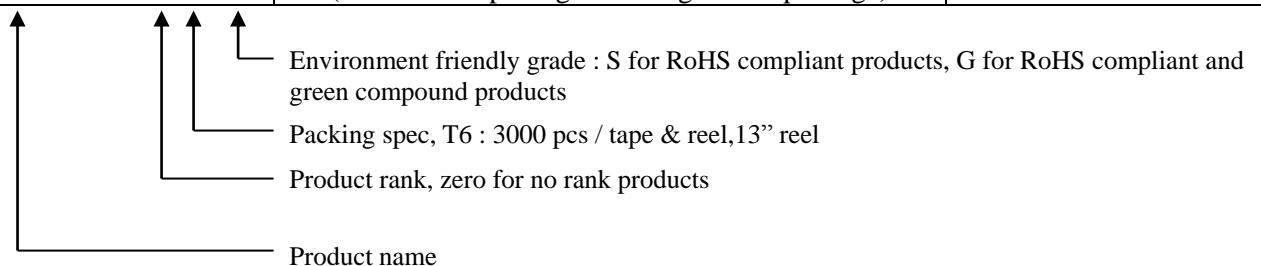


**Outline**



**Ordering Information**

| Device              | Package   | Shipping               |
|---------------------|---|------------------------|
| MTB7D5N10RH8-0-T6-G | DFN 5 ×6<br>(Pb-free lead plating and halogen-free package) | 3000 pcs / tape & reel |





**Absolute Maximum Ratings** (Ta=25°C)

| Parameter   | Symbol                            | 10s                            | Steady State | Unit |    |
|---|-----------------------------------|--------------------------------|--------------|------|----|
| Drain-Source Voltage  | V <sub>DS</sub>                   | 110                            |              | V    |    |
| Gate-Source Voltage   | V <sub>GS</sub>                   | ±20                            |              |      |    |
| Continuous Drain Current @ T <sub>C</sub> =25°C, V <sub>GS</sub> =10V (Note 1)  | I <sub>D</sub>                    | 53                             |              | A    |    |
| Continuous Drain Current @ T <sub>C</sub> =100°C, V <sub>GS</sub> =10V (Note 1) |                                   | 33.5                           |              |      |    |
| Continuous Drain Current @ T <sub>A</sub> =25°C, V <sub>GS</sub> =10V (Note 2)  | I <sub>DSM</sub>                  | 17.8                           | 11.8         |      |    |
| Continuous Drain Current @ T <sub>A</sub> =70°C, V <sub>GS</sub> =10V (Note 2)  |                                   | 14.2                           | 9.4          |      |    |
| Continuous Drain Current @ T <sub>A</sub> =85°C, V <sub>GS</sub> =10V (Note 2)  |                                   | 12.8                           | 8.5          |      |    |
| Pulsed Drain Current (Note 3)   |                                   | I <sub>DM</sub>                | 212 *1       |      |    |
| Avalanche Current @ L=0.1mH (Note 3)  | I <sub>AS</sub>                   | 50                             |              |      | mJ |
| Avalanche Energy @ L=1mH, I <sub>D</sub> =20A, V <sub>DD</sub> =25V (Note 4)    | E <sub>AS</sub>                   | 200                            |              |      |    |
| Repetitive Avalanche Energy @ L=0.05mH (Note 3)                                 | E <sub>AR</sub>                   | 5 *2                           |              |      |    |
| Total Power Dissipation   | P <sub>D</sub>                    | T <sub>C</sub> =25°C (Note 1)  | 50           |      | W  |
|   |                                   | T <sub>C</sub> =100°C (Note 1) | 20           |      |    |
|   | P <sub>DSM</sub>                  | T <sub>A</sub> =25°C (Note 2)  | 5.7          | 2.5  |    |
|   |                                   | T <sub>A</sub> =70°C (Note 2)  | 4.0          | 1.8  |    |
|   |                                   | T <sub>A</sub> =85°C (Note 2)  | 3.6          | 1.6  |    |
| Operating Junction and Storage Temperature Range                                | T <sub>J</sub> , T <sub>stg</sub> | -55~+150                       |              | °C   |    |

**Thermal Data**

| Parameter  | Symbol           | Typical      | Maximum | Unit |      |
|--|------------------|--------------|---------|------|------|
| Thermal Resistance, Junction-to-ambient (Note 2) | R <sub>θJA</sub> | t≤10s        | 18      | 22   | °C/W |
|  |                  | Steady State | 42      | 50   |      |
| Thermal Resistance, Junction-to-case             | R <sub>θJC</sub> | 2            | 2.5     |      |      |

- Note : 1.The power dissipation P<sub>D</sub> is based on T<sub>J(MAX)</sub>=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
- 2.The value of R<sub>θJA</sub> is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2 oz. copper, in a still air environment with T<sub>A</sub>=25°C. The power dissipation P<sub>DSM</sub> is based on R<sub>θJA</sub> and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
- 3.Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and low duty cycles to keep initial T<sub>J</sub>=25°C.
- 4.100% tested by conditions of L=0.1mH, I<sub>AS</sub>=20A, V<sub>GS</sub>=10V, V<sub>DD</sub>=25V



**Characteristics (Tj=25°C, unless otherwise specified)**

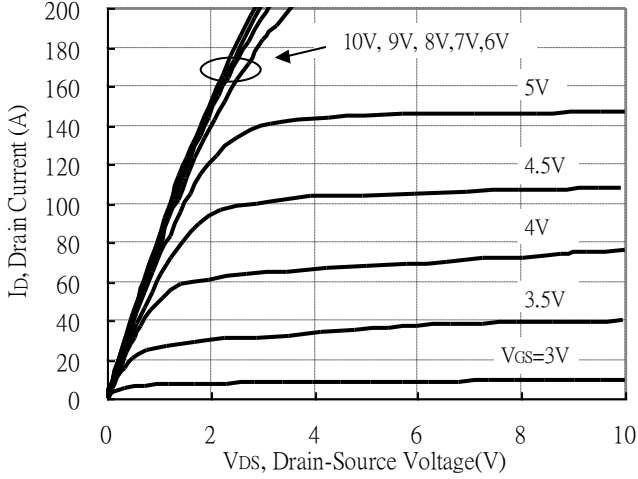
| Symbol                              | Min. | Typ. | Max. | Unit | Test Conditions  |
|-------------------------------------|------|------|------|------|--|
| <b>Static</b>                       |      |      |      |      |  |
| BV <sub>DSS</sub>                   | 110  | -    | -    | V    | V <sub>GS</sub> =0V, I <sub>D</sub> =250μA   |
| ΔBV <sub>DSS</sub> /ΔT <sub>j</sub> | -    | 0.08 | -    | V/°C | Reference to 25°C, I <sub>D</sub> =250μA   |
| V <sub>GS(th)</sub>                 | 1.5  | -    | 2.5  | V    | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA                            |
| *G <sub>FS</sub>                    | -    | 40   | -    | S    | V <sub>DS</sub> =5V, I <sub>D</sub> =20A   |
| I <sub>GSS</sub>                    | -    | -    | ±100 | nA   | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V   |
| I <sub>DSS</sub>                    | -    | -    | 1    | μA   | V <sub>DS</sub> =90V, V <sub>GS</sub> =0V  |
|                                     | -    | -    | 25   |      | V <sub>DS</sub> =90V, V <sub>GS</sub> =0V, T <sub>j</sub> =125°C                     |
| *R <sub>DS(ON)</sub>                | -    | 6.4  | 9    | mΩ   | V <sub>GS</sub> =10V, I <sub>D</sub> =20A  |
|                                     | -    | 9.3  | 14   |      | V <sub>GS</sub> =4.5V, I <sub>D</sub> =16A   |
| <b>Dynamic</b>                      |      |      |      |      |  |
| *Q <sub>g</sub>                     | -    | 53.9 | -    | nC   | V <sub>DS</sub> =80V, I <sub>D</sub> =20A, V <sub>GS</sub> =10V                      |
| *Q <sub>gs</sub>                    | -    | 12.3 | -    |      |  |
| *Q <sub>gd</sub>                    | -    | 10   | -    |      |  |
| *t <sub>d(ON)</sub>                 | -    | 26.6 | -    | ns   | V <sub>DS</sub> =50V, I <sub>D</sub> =13A, V <sub>GS</sub> =10V, R <sub>GS</sub> =6Ω |
| *t <sub>r</sub>                     | -    | 8.2  | -    |      |  |
| *t <sub>d(OFF)</sub>                | -    | 72.4 | -    |      |  |
| *t <sub>f</sub>                     | -    | 14.4 | -    |      |  |
| C <sub>iss</sub>                    | -    | 3480 | -    | pF   | V <sub>GS</sub> =0V, V <sub>DS</sub> =50V, f=1MHz                                    |
| C <sub>oss</sub>                    | -    | 315  | -    |      |  |
| C <sub>rss</sub>                    | -    | 29   | -    |      |  |
| R <sub>g</sub>                      | -    | 0.9  | -    |      |  |
| <b>Source-Drain Diode</b>           |      |      |      |      |  |
| *I <sub>S</sub>                     | -    | -    | 40   | A    |  |
| *I <sub>SM</sub>                    | -    | -    | 160  |      |  |
| *V <sub>SD</sub>                    | -    | 0.84 | 1.2  | V    | I <sub>S</sub> =20A, V <sub>GS</sub> =0V   |
| *t <sub>rr</sub>                    | -    | 45.2 | -    | ns   | V <sub>GS</sub> =0V, I <sub>F</sub> =13A, dI <sub>F</sub> /dt=100A/μs                |
| *Q <sub>rr</sub>                    | -    | 81.9 | -    | nC   |  |

\*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

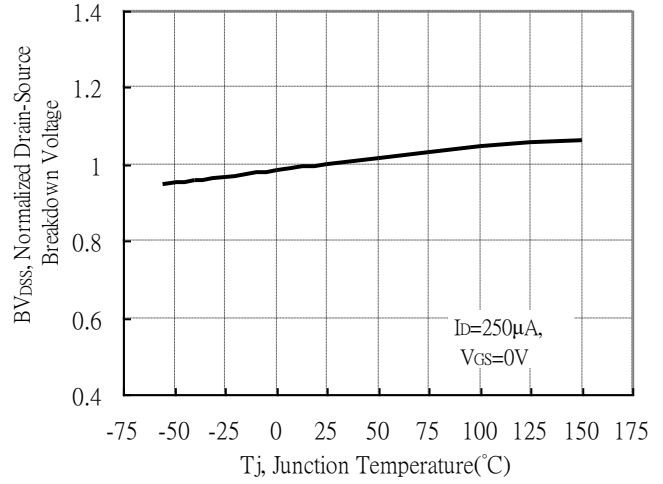


**Typical Characteristics**

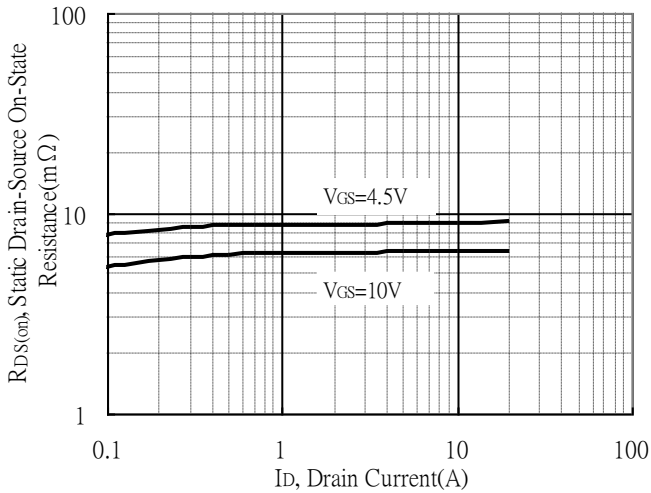
Typical Output Characteristics



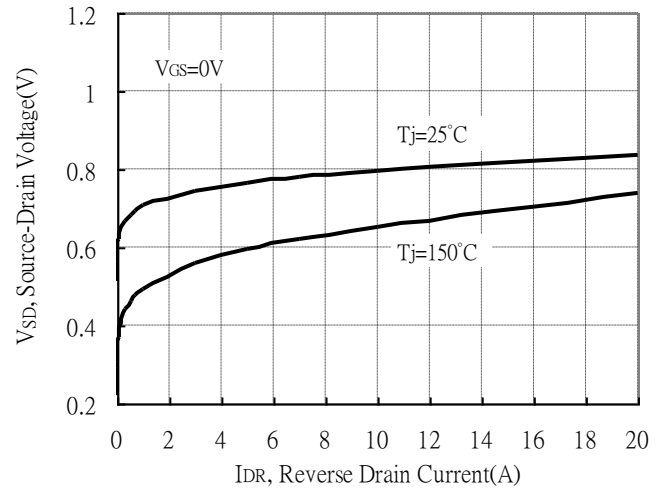
Brekdown Voltage vs Ambient Temperature



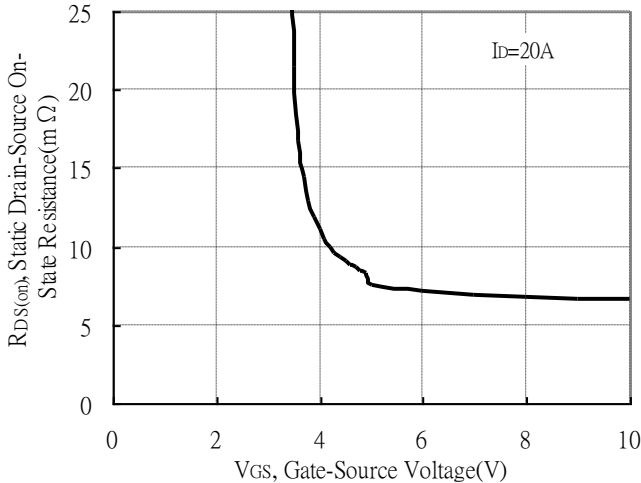
Static Drain-Source On-State resistance vs Drain Current



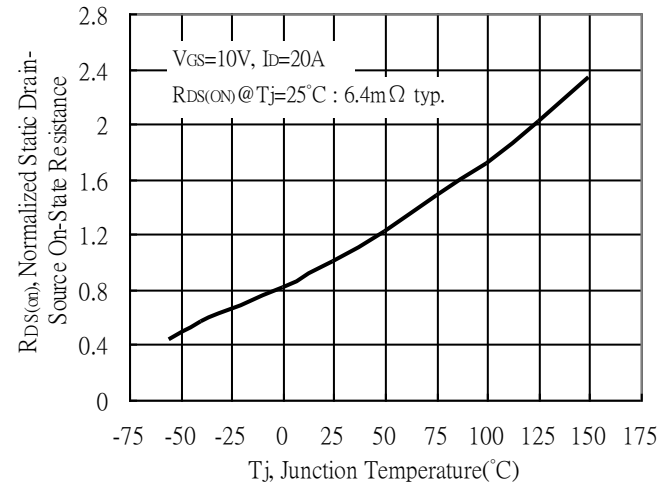
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

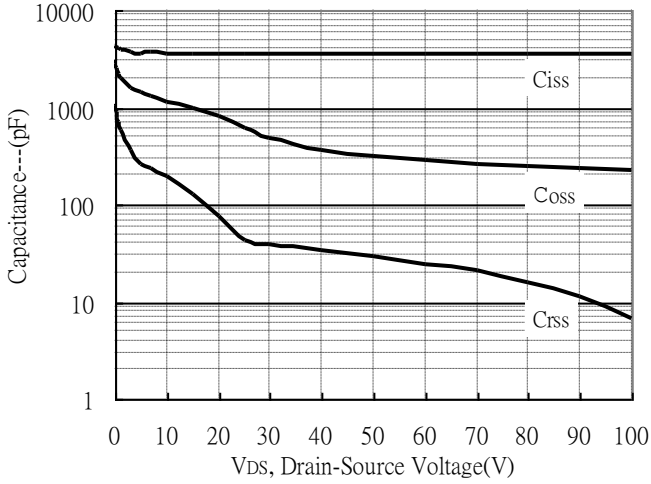


Drain-Source On-State Resistance vs Junction Temperature

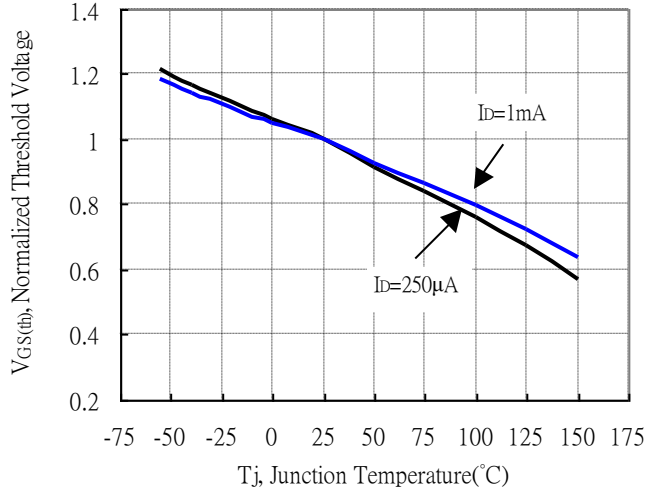


**Typical Characteristics(Cont.)**

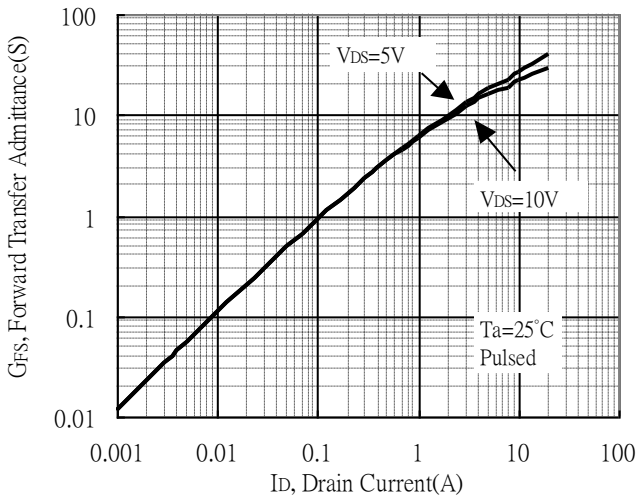
Capacitance vs Drain-to-Source Voltage



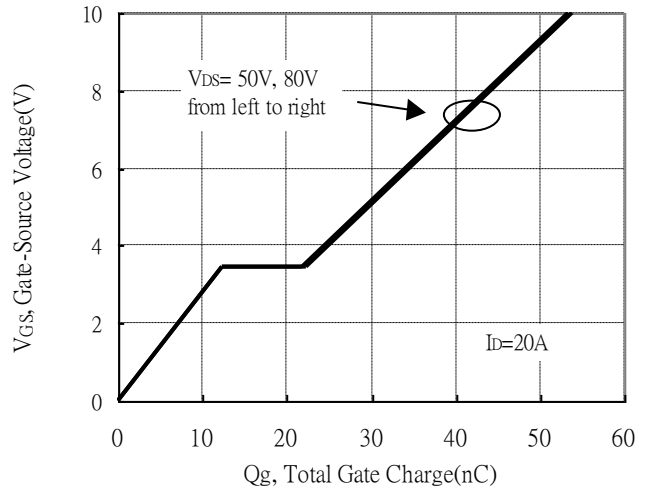
Threshold Voltage vs Junction Temperature



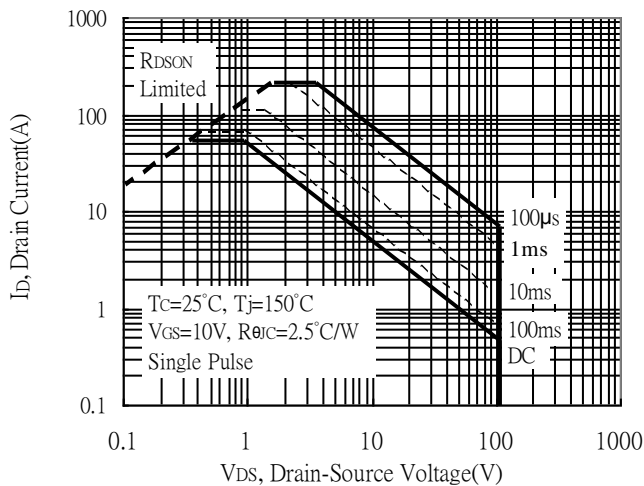
Forward Transfer Admittance vs Drain Current



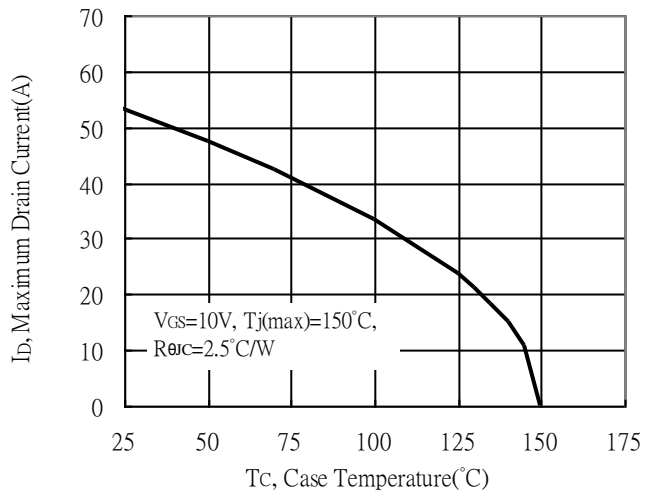
Gate Charge Characteristics



Maximum Safe Operating Area



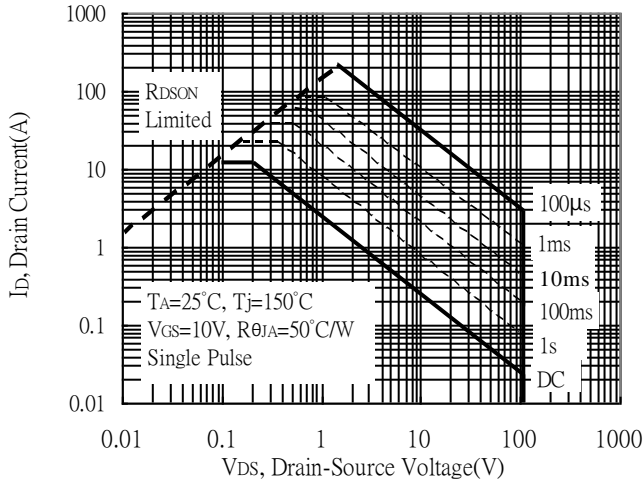
Maximum Drain Current vs Case Temperature



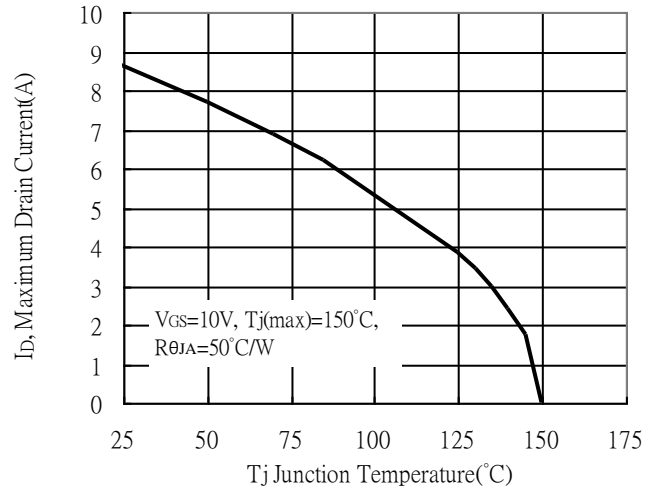


### Typical Characteristics (Cont.)

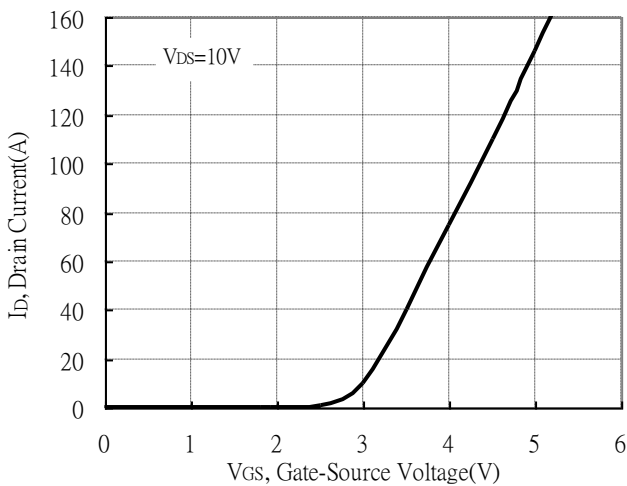
Maximum Safe Operating Area



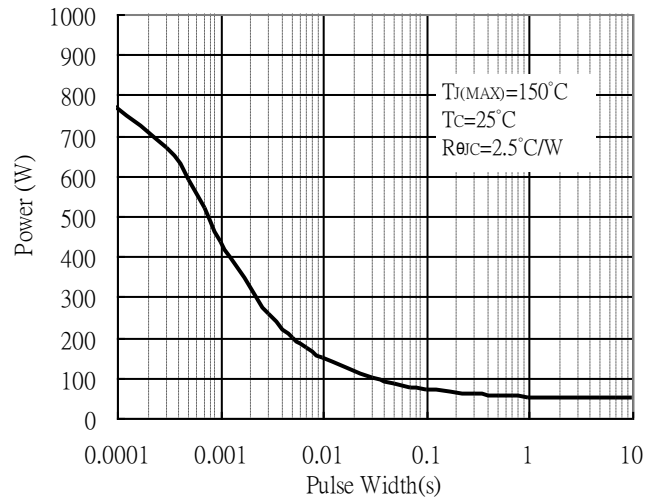
Maximum Drain Current vs Junction Temperature



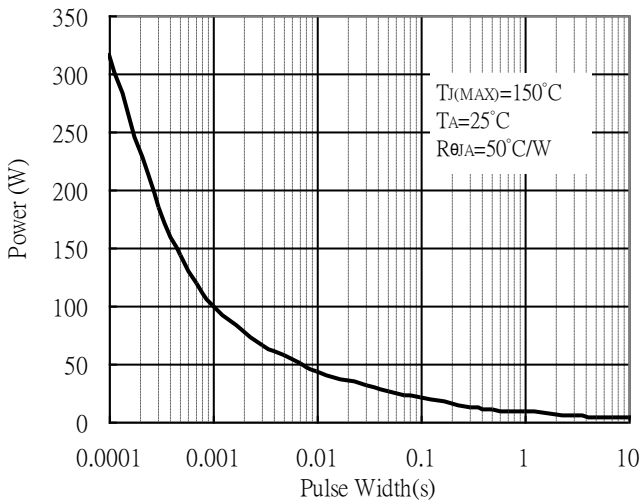
Typical Transfer Characteristics



Single Pulse Power Rating, Junction to Case

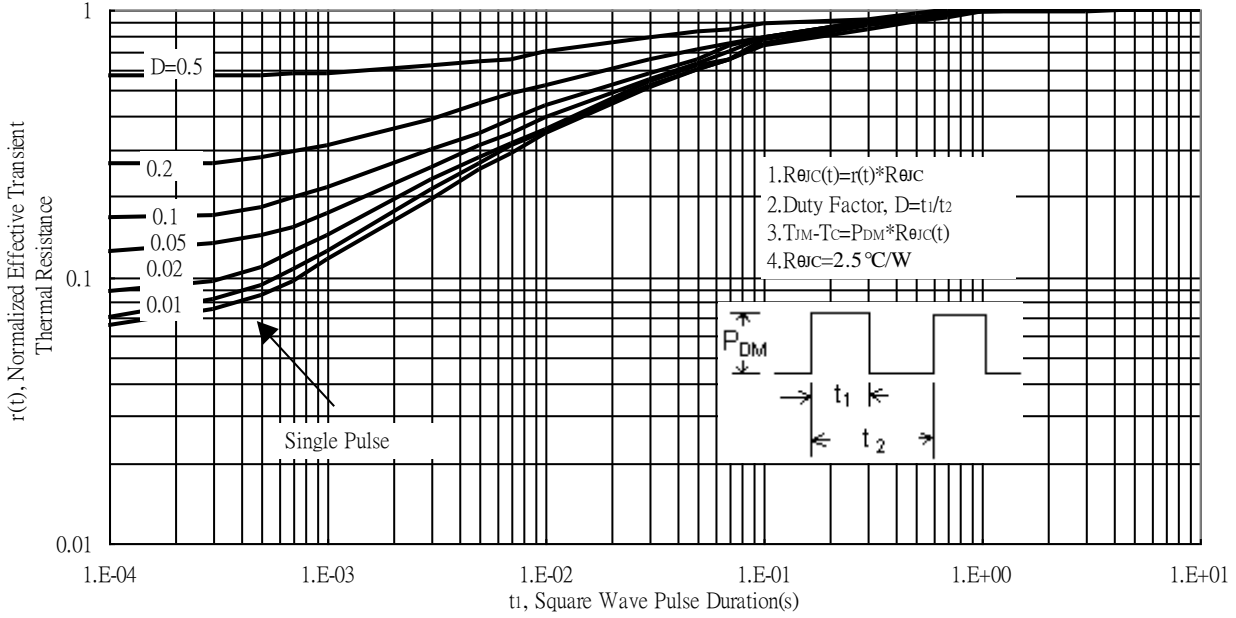


Single Pulse Power Rating, Junction to Case

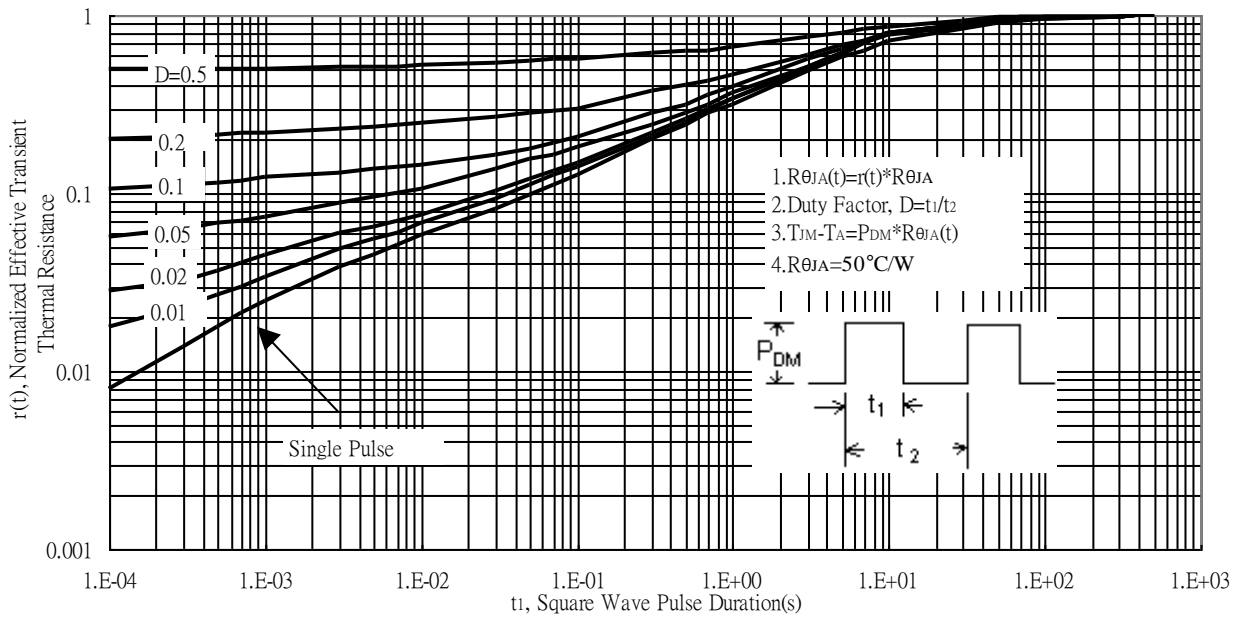


**Typical Characteristics (Cont.)**

Transient Thermal Response Curves

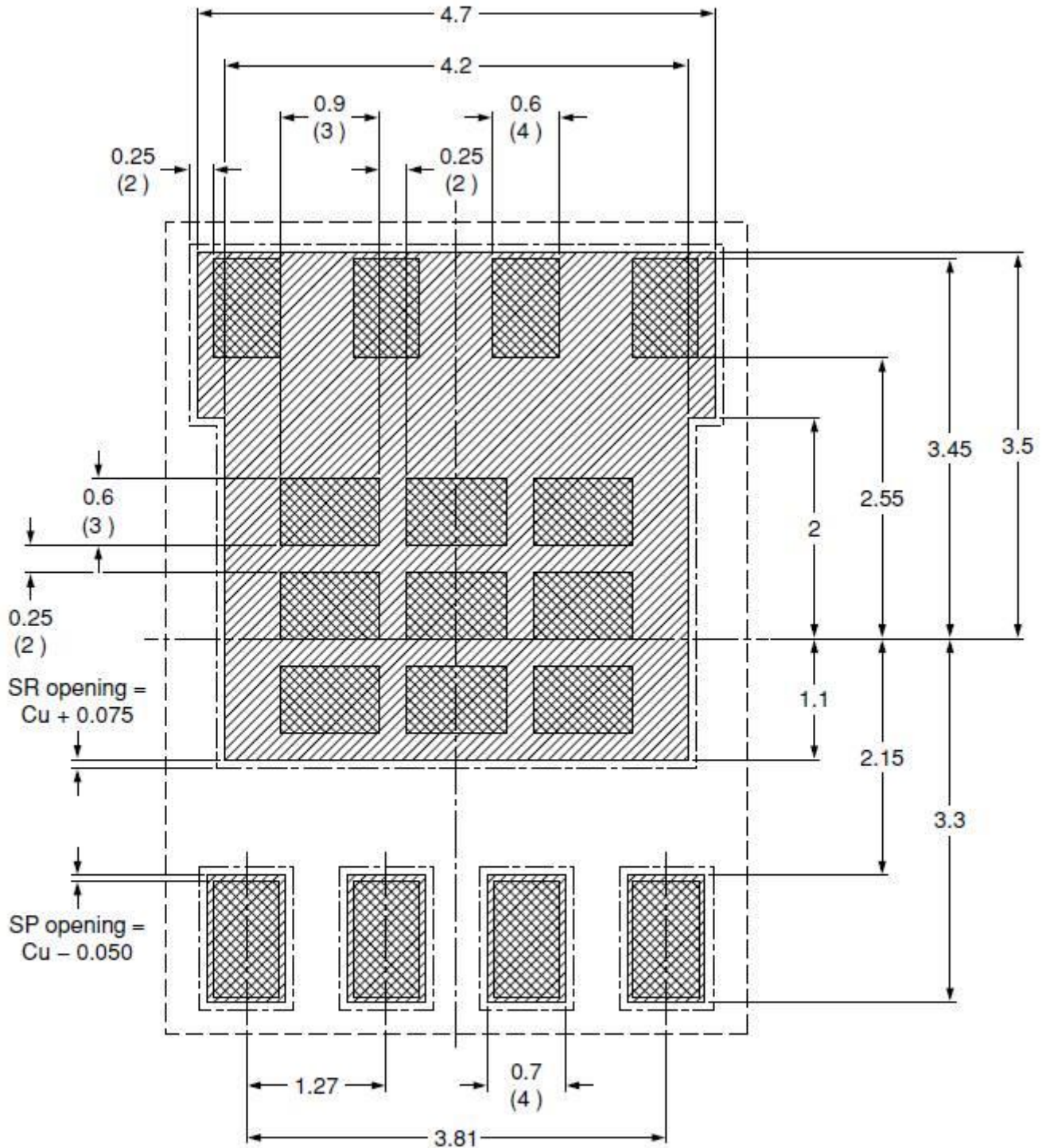




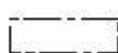
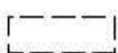
Transient Thermal Response Curves





**Recommended Soldering Footprint & Stencil Design**

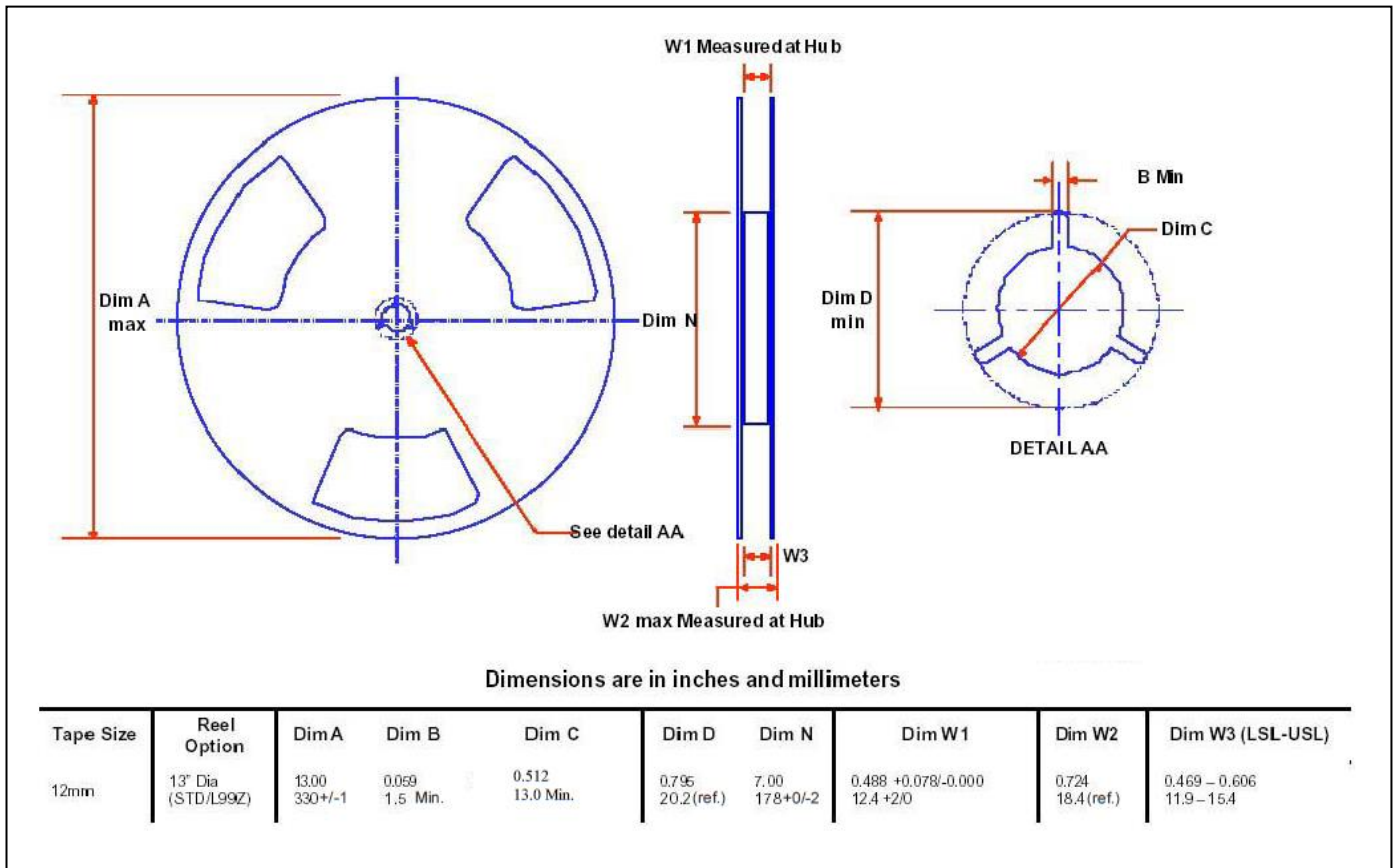


- |   |  |
|---|--|
|  solder lands  |  solder paste<br>125 μm stencil |
|  solder resist |  occupied area                  |

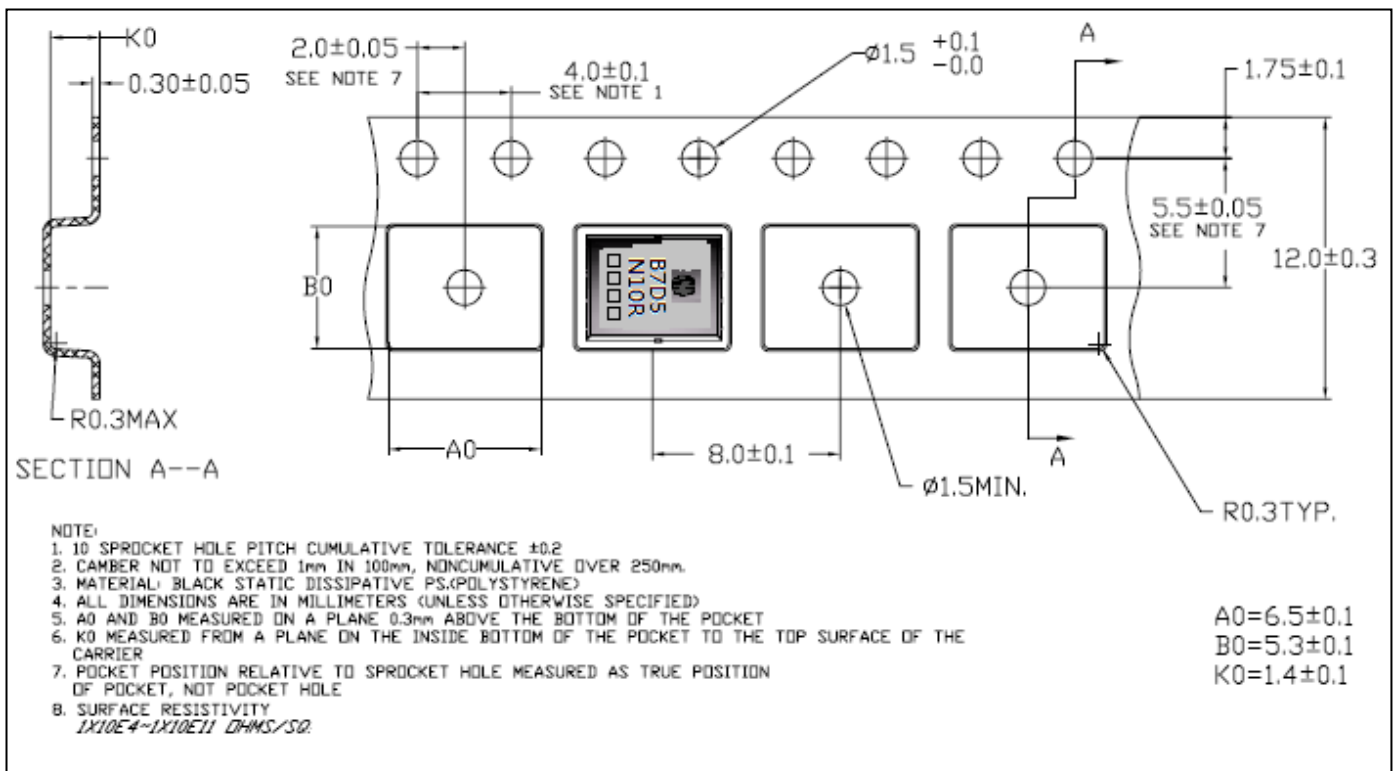
unit : mm



**Reel Dimension**



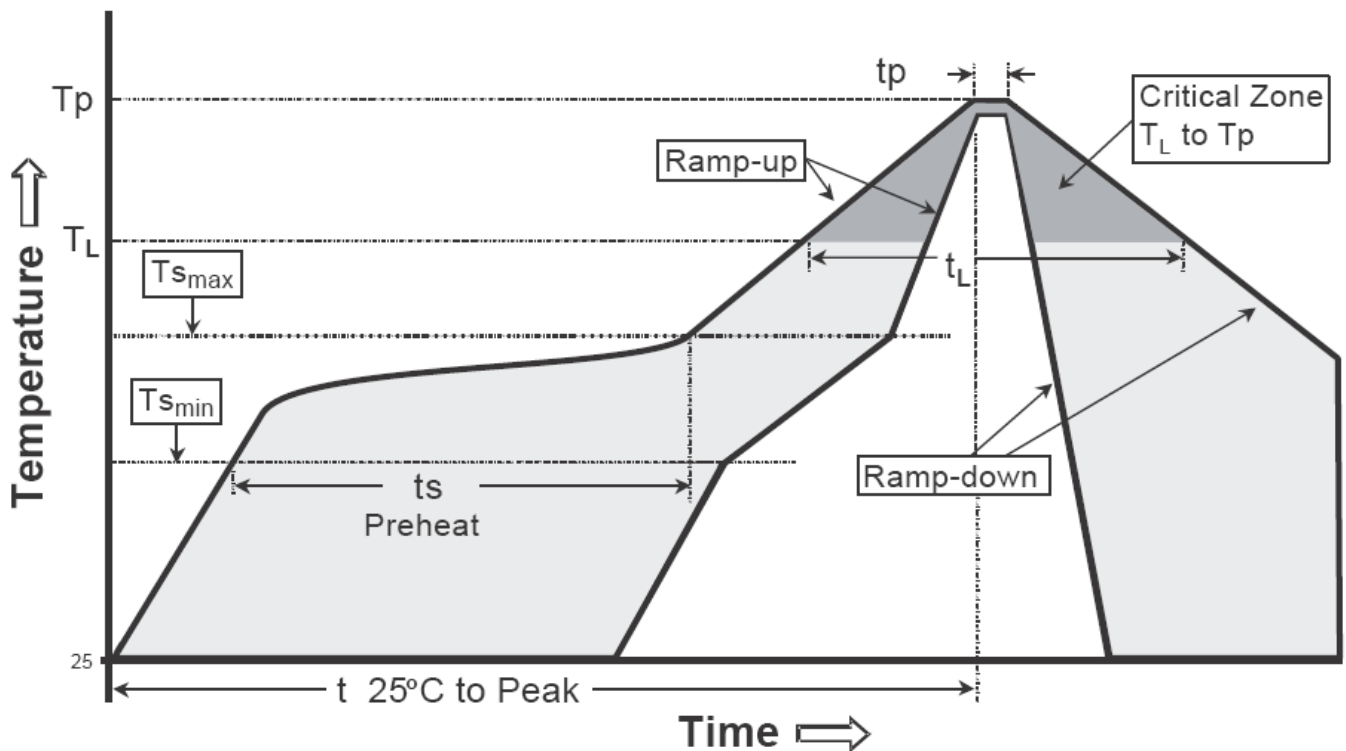
**Carrier Tape Dimension**



**Recommended wave soldering condition**

|                 |                  |                 |
|-----------------|------------------|-----------------|
| Product         | Peak Temperature | Soldering Time  |
| Pb-free devices | 260 +0/-5 °C     | 5 +1/-1 seconds |

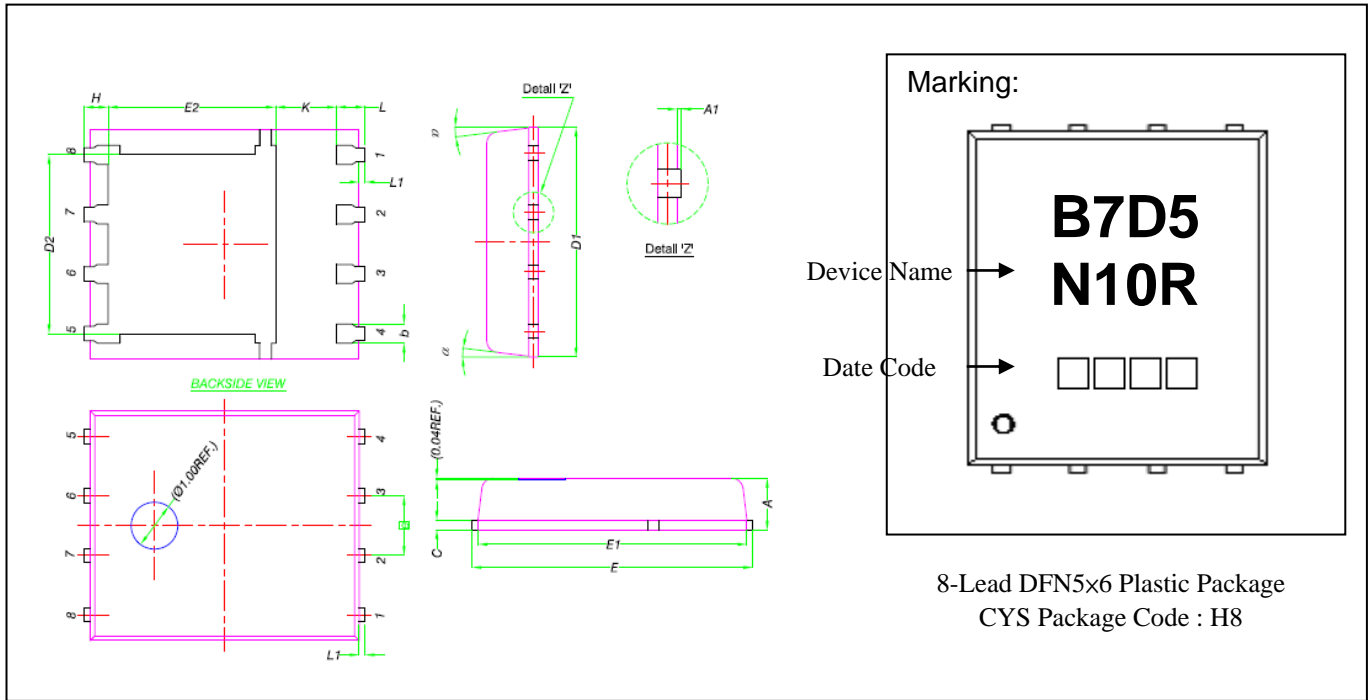
**Recommended temperature profile for IR reflow**



| Profile feature   | Sn-Pb eutectic Assembly | Pb-free Assembly |
|---|-------------------------|------------------|
| Average ramp-up rate (T <sub>smax</sub> to T <sub>p</sub> ) | 3°C/second max.         | 3°C/second max.  |
| Preheat   |                         |                  |
| -Temperature Min(T <sub>s min</sub> )                       | 100°C                   | 150°C            |
| -Temperature Max(T <sub>s max</sub> )                       | 150°C                   | 200°C            |
| -Time(t <sub>s min</sub> to t <sub>s max</sub> )            | 60-120 seconds          | 60-180 seconds   |
| Time maintained above:                                      |                         |                  |
| -Temperature (T <sub>L</sub> )                              | 183°C                   | 217°C            |
| - Time (t <sub>L</sub> )                                    | 60-150 seconds          | 60-150 seconds   |
| Peak Temperature(T <sub>p</sub> )                           | 240 +0/-5 °C            | 260 +0/-5 °C     |
| Time within 5°C of actual peak temperature(t <sub>p</sub> ) | 10-30 seconds           | 20-40 seconds    |
| Ramp down rate  | 6°C/second max.         | 6°C/second max.  |
| Time 25 °C to peak temperature                              | 6 minutes max.          | 8 minutes max.   |

Note : All temperatures refer to topside of the package, measured on the package body surface.

**DFN5x6 Dimension**



| DIM | Millimeters |      | Inches |       | DIM | Millimeters |      | Inches |       |
|-----|-------------|------|--------|-------|-----|-------------|------|--------|-------|
|     | Min.        | Max. | Min.   | Max.  |     | Min.        | Max. | Min.   | Max.  |
| A   | 0.90        | 1.10 | 0.035  | 0.043 | E2  | 3.38        | 3.78 | 0.133  | 0.149 |
| A1  | 0.00        | 0.05 | 0.000  | 0.002 | e   | 1.27        | BSC  | 0.050  | BSC   |
| b   | 0.33        | 0.51 | 0.013  | 0.020 | H   | 0.41        | 0.61 | 0.016  | 0.024 |
| C   | 0.20        | 0.30 | 0.008  | 0.012 | K   | 1.10        | -    | 0.043  | -     |
| D1  | 4.80        | 5.00 | 0.189  | 0.197 | L   | 0.51        | 0.71 | 0.020  | 0.028 |
| D2  | 3.61        | 3.96 | 0.142  | 0.156 | L1  | 0.06        | 0.20 | 0.002  | 0.008 |
| E   | 5.90        | 6.10 | 0.232  | 0.240 | θ   | 8°          | 12°  | 8°     | 12°   |
| E1  | 5.70        | 5.80 | 0.224  | 0.228 |     |             |      |        |       |

**Notes:** 1.Controlling dimension: millimeters.  
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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